

ALD of Al₂O₃ for gas barrier applications: Impact of Al precursors

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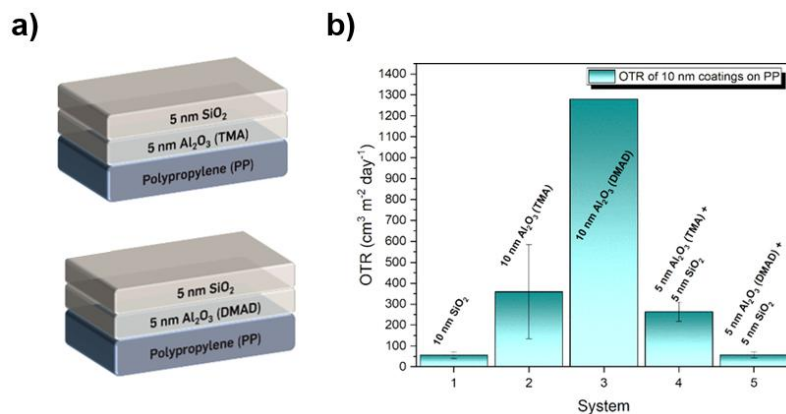


Figure 1. a) Scheme of the dyads consisting of Al₂O₃ grown with TMA (top) and DMAD (bottom) b) Oxygen transmission rates (OTR) of different Al₂O₃ and SiO₂ GBLs on PP foil.^[4]

Literature:

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